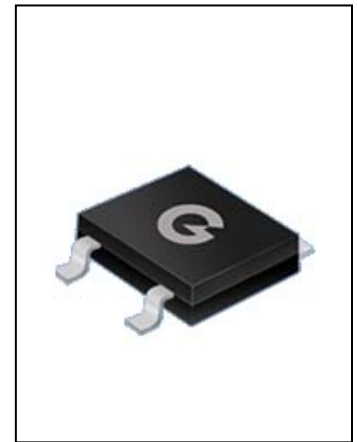


SILICON BRIDGE RECTIFIERS**EDB101S--EDB106S****SFEATURES**

- Rating to 1000V PRVP
- Surge overload rating to 30 Amperes peak
- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- Lead solderable per MIL-STD-202 method 208
- Glass passivated chip junctions
- Plastic material has UL flammability classification94V-0
- Polarity symbols molded on body

**Maximum Ratings** (@TA = 25°C unless otherwise specified)

Characteristic	Symbol	EDB101S	EDB102S	EDB103S	EDB104S	EDB105S	EDB106S	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	50	100	150	200	300	400	V
RMS Reverse Voltage	V_{RMS}	35	70	105	140	210	280	V
DC Blocking Voltage	V_{DC}	50	100	150	200	300	400	V
Maximum average forward Output current @TA=55°C	$I_{F(AV)}$	1.0						A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	I_{FSM}	30						A

Thermal Characteristics

Characteristic	Symbol	EDB101S	EDB102S	EDB103S	EDB104S	EDB105S	EDB106S	UNITS
Typical junction calacitance (NOTE 2)	C_J	15				10		pF
Operating junction temperature range	T_J	- 55 ---- + 150						°C
Storage temperature range	T_{STG}	- 55 ---- + 150						°C

Electrical Characteristics (@TA = 25°C unless otherwise specified)

Characteristic	Symbol	EDB101S	EDB102S	EDB103S	EDB104S	EDB105S	EDB106S	UNITS
Maximum instantaneous forward voltage at 1.0 A	V_F	1.0						V
Maximum reverse current @TA=25°C at rated DC blocking voltage @TA=100°C	I_R	10.0			1.0			μ A mA
Maximum reverse recovery time (NOTE 1)	t_{rr}	50						ns

NOTE: 1. Test conditions: $I_F=0.5A$, $I_R=-1.0A$, $IRR=-0.25A$.

2. Measured at 1 MHz and applied reverse voltage of 4.0 v olts.



SILICON BRIDGE RECTIFIERS

EDB101S--EDB106S

PACKAGE OUTLINE DIMENSIONS

DFS		
Dim	Min	Max
A	8.20	8.60
B	6.10	6.50
C	2.35	2.65
D	9.80	10.20
E	0.15	0.35
F	0.90	1.50
G	0.20MAX	
H	2.50	2.80
I	1.00	1.40
K	4.80	5.20
All Dimensions in mm		

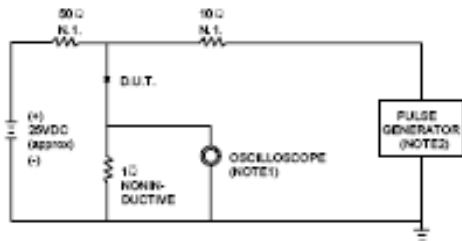
PACKAGE INFORMATION

Device	Package	Shipping
EDB101S--EDB106S	DFS	50unit/pipe

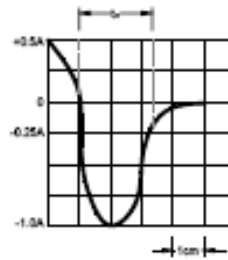
SILICON BRIDGE RECTIFIERS

EDB101S--EDB106S

FIG.1 – TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES: 1. RISE TIME = 7ns MAX. INPUT IMPEDANCE = 1MΩ, 22pF
2. RISE TIME = 10ns MAX. SOURCE IMPEDANCE = 50Ω



SET TIME BASE FOR
10 ns /cm

FIG.2 – TYPICAL FORWARD CURRENT DERATING CURVE

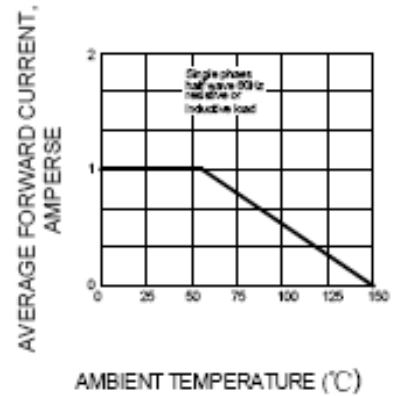


FIG.3 – TYPICAL REVERSE CHARACTERISTICS

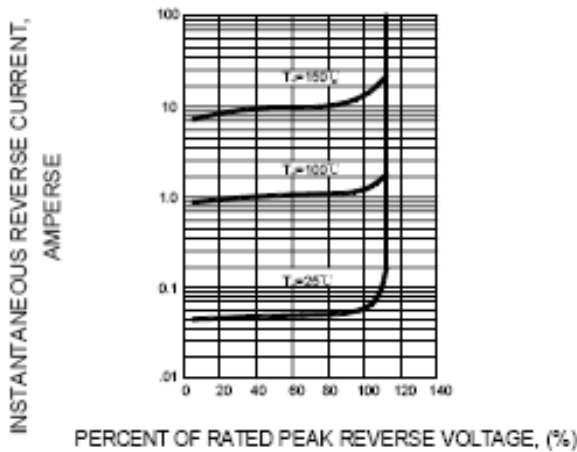


FIG.4 -- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

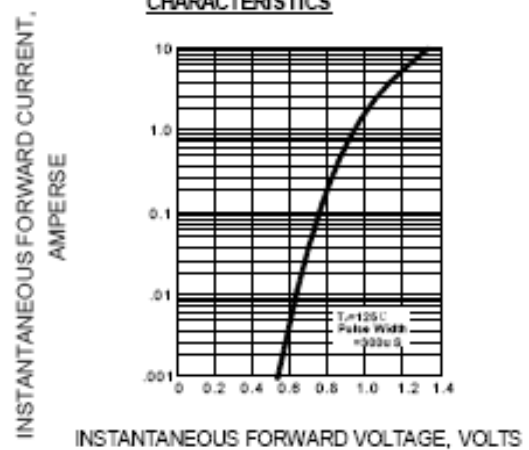


FIG.5 – MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

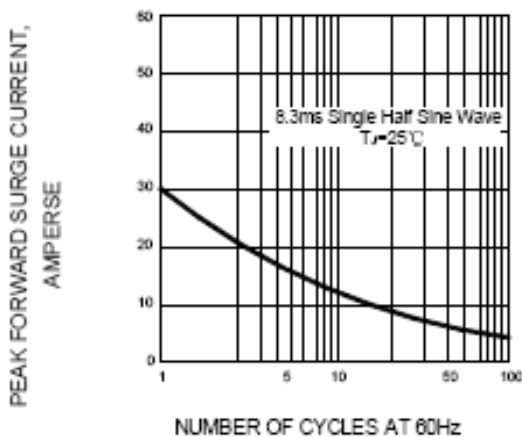


FIG.6 – TYPICAL JUNCTION CAPACITANCE

